General Purpose Transistors

PNP Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

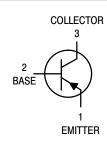
DEVICE MARKING

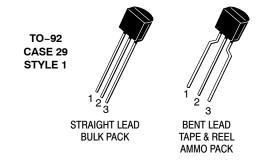
Device	Line 1	Line 2
MPS2907AG	MPS	2907A
MPS2907ARLG	MPS2	907A
MPS2907ARLRAG	MPS	2907
MPS2907ARLRPG	MPS	2907



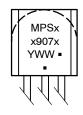
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

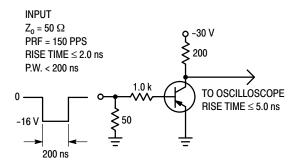
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS			l .		
Collector - Emitter Breakdown Voltage	V _{(BR)CEO}	-60	-	Vdc	
Collector – Base Breakdown Voltage (I _C	; = -10 μAdc, I _E = 0)	V _{(BR)CBO}	-60	-	Vdc
Emitter – Base Breakdown Voltage (I _E =	-10 μAdc, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CE} = -30 Vd	c, V _{EB(off)} = -0.5 Vdc)	I _{CEX}	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$			- -	-0.01 -10	μAdc
Base Current (V _{CE} = -30 Vdc, V _{EB(off)}	= -0.5 Vdc)	I _B	-	-50	nAdc
ON CHARACTERISTICS		•		•	•
DC Current Gain $ \begin{array}{l} (I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ (I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ (Note 1) \end{array} $		h _{FE}	75 100 100 100 50	- - - 300 -	-
Collector – Emitter Saturation Voltage (Note 1) (I _C = -150 mAdc, I _B = -15 mAdc) (I _C = -500 mAdc, I _B = -50 mAdc)		V _{CE(sat)}	- -	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 1)		V _{BE(sat)}	- -	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS	3		l .	I.	
Current – Gain – Bandwidth Product (Notes 1 and 2), (I _C = -50 mAdc, V _{CE} = -20 Vdc, f = 100 MHz)		f _T	200	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	30	pF
SWITCHING CHARACTERISTICS					
Turn-On Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc},$	t _{on}	-	45	ns
Delay Time	$I_{B1} = -15$ mAdc) (Figures 1 and 5)	t _d	-	10	ns
Rise Time		t _r	-	40	ns
Turn-Off Time	$(V_{CC} = -6.0 \text{ Vdc}, I_{C} = -150 \text{ mAdc},$	t _{off}	-	100	ns
Storage Time	I _{B1} = I _{B2} = 15 mAdc) (Figure 2)	t _s	-	80	ns
Fall Time		t _f	-	30	ns

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



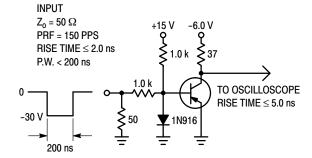


Figure 1. Delay and Rise Time Test Circuit

Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

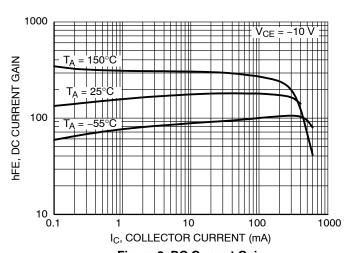


Figure 3. DC Current Gain

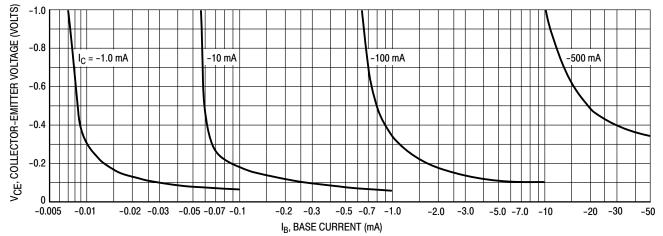


Figure 4. Collector Saturation Region

ORDERING INFORMATION

Device	Package	Shipping [†]	
MPS2907AG	TO-92 (Pb-Free)	5000 Units / Bulk	
MPS2907ARLG	TO-92 (Pb-Free)	anno (Terre & Berel	
MPS2907ARLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel	
MPS2907ARLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

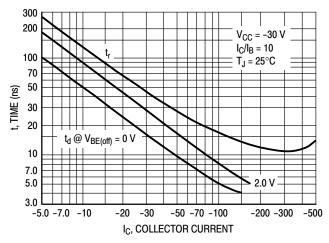


Figure 5. Turn-On Time

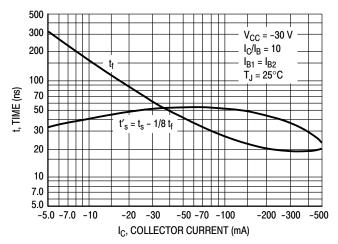


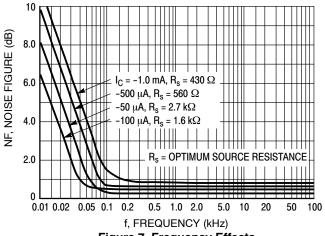
Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C

10

50 100 200



8.0 I_C = -50 µA -100 µA -500 µA -1.0 mA

1.0 k

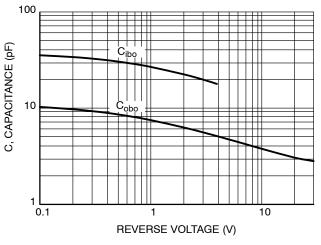
Figure 7. Frequency Effects

 $R_{\text{s}},$ SOURCE RESISTANCE (Ω) Figure 8. Source Resistance Effects

2.0 k

5.0 k

50 k



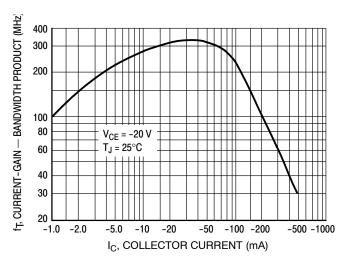
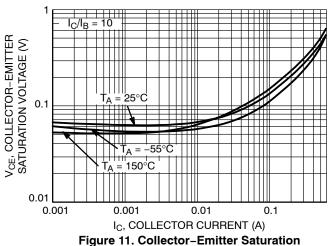


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



Voltage vs. Collector Current

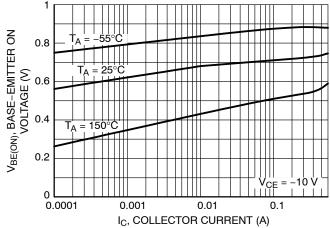
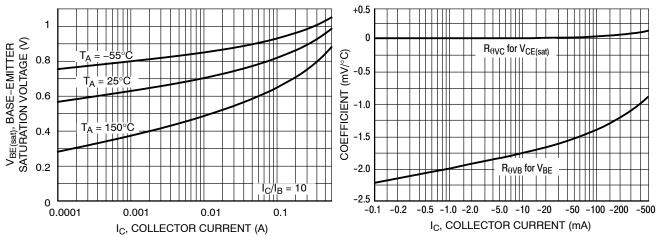


Figure 12. Base-Emitter Turn-ON Voltage vs.
Collector Current



I_C, COLLECTOR CURRENT (A)

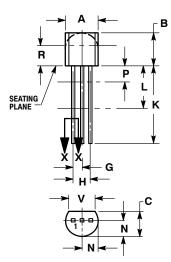
Figure 13. Base Emitter Saturation Voltage vs.

Collector Current

Figure 14. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



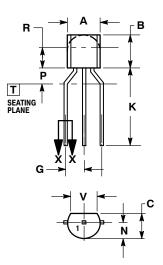
STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS. CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	2 //2		

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

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SMUN5335DW1T1G NSBA114YF3T5G NSBC114TF3T5G